	Type	L #	Hits	Search Text	DBs	Comments
1	BRS	L1	281283	257/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
2	BRS	L2	23378	1 and (CMOS or (complimentary near metal-oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
3	BRS	L3	293	2 and (trim$4 or etch$3 or remov$3 or nitridiz$3 ot oxidiz$3) near ((polysilicon or conductive or poly) near gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4	BRS	L4	87	3 and (gate near (width or length or height))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
5	BRS	L5	416	(furukawa-toshiharu or hakey-mark-c or holmes-steven-j or horak-david-v or rabidoux-paul-a).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
6	BRS	L6	11	5 and (trim$4 or etch$3 or remov$3 or nitridiz$3 ot oxidiz$3) near ((polysilicon or conductive or poly) near gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
7	BRS	L7	27	((trim$4 or etch$3 or remov$3 or nitridiz$3 ot oxidiz$3) near ((polysilicon or conductive or poly) near gate)).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
8	BRS	L8	924	((trim$4 or etch$3 or remov$3 or nitridiz$3 ot oxidiz$3) near ((polysilicon or conductive or poly) near gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
9	BRS	L9	3	8 and (different near (size or width or height or length) near gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
10	BRS	L11	357	8 and CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
11	BRS	L13	2	12 and surface near (oxidation or nitridation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
12	BRS	L12	159	11 and ((thickness or width or height or length) near gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	

	Type	L #	Hits	Search Text	DBs	Comments
13	BRS	L14	1098	(smaller or longer) near ((size or width or height or length) near gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
14	BRS	L15	424	14 and CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
15	BRS	L16	4	15 and (oxididation or nitridation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
16	BRS	L17	191	15 and isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
17	BRS	L19	8	18 and (trim$4 or etch$3 or remov$3 or nitridiz$3 ot oxidiz$3) near ((polysilicon or conductive or poly) near gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
18	BRS	L18	117	17 and (gate near (oxide or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	